Icemos Technology Ltd **Product Specification** **1003.726001** Issue Date 08 May 2025 21:36:4

Part Number	Customer

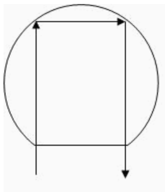
Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	500.00 +/- 2.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<1.00µm	Guaranteed by Process
	7.0	Bow	<40.00µm	ADE to ASTM F534, 20%
	8.0	Warp	<40.00µm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100% (note 2)
	10.0	Edge Exclusion	3mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{100} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	500.00 +/- 2.00 µm	ADE, 100%
	14.0	Handle Doping Type	P	Wafer Vendor
	15.0	Handle Dopant	Boron	Wafer Vendor
	16.0	Handle Resistivity	0.1 - 1 Ohmcm	Wafer Vendor
	17.0	Backside Finish	Polished with light handling marks as per comments & Lasermark	Guaranteed by process
	18.0	Total scratch length	Frontside - Total <10mm.	Bright Light, 100% (note2)
	19.0	Surface Haze	none	Bright Light, 100% (note 2)

Part Number Customer

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

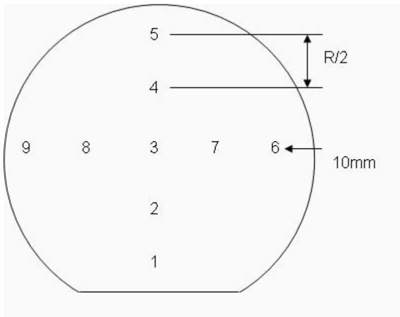
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information